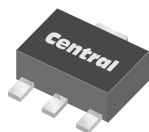


CXTA62

**SURFACE MOUNT
PNP SILICON
DARLINGTON TRANSISTOR**



SOT-89 CASE



www.centrasemi.com

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CXTA62 is a PNP Silicon Darlington transistor manufactured by the epitaxial planar process, epoxy molded in a surface mount package, designed for applications requiring extremely high gain.

MARKING: FULL PART NUMBER

MAXIMUM RATINGS: ($T_A=25^{\circ}\text{C}$)

Collector-Base Voltage
Collector-Emitter Voltage
Emitter-Base Voltage
Continuous Collector Current
Power Dissipation
Operating and Storage Junction Temperature
Thermal Resistance

SYMBOL

V_{CB0}	20
V_{CES}	20
V_{EBO}	10
I_C	500
P_D	1.2
T_J, T_{stg}	-65 to +150
θ_{JA}	104

UNITS

V
V
V
mA
W
$^{\circ}\text{C}$
$^{\circ}\text{C/W}$

ELECTRICAL CHARACTERISTICS: ($T_A=25^{\circ}\text{C}$)

SYMBOL TEST CONDITIONS

I_{CBO}	$V_{CB}=15\text{V}$
I_{EBO}	$V_{EB}=10\text{V}$
BV_{CES}	$I_C=100\mu\text{A}$
BV_{CBO}	$I_C=100\mu\text{A}$
$V_{CE(SAT)}$	$I_C=10\text{mA}, I_B=10\mu\text{A}$
$V_{BE(ON)}$	$V_{CE}=5.0\text{V}, I_C=10\text{mA}$
h_{FE}	$V_{CE}=5.0\text{V}, I_C=10\text{mA}$

MIN

20
20

20K

MAX

100
100
1.0
1.4

UNITS

nA
nA
V
V
V
V

CXTA62

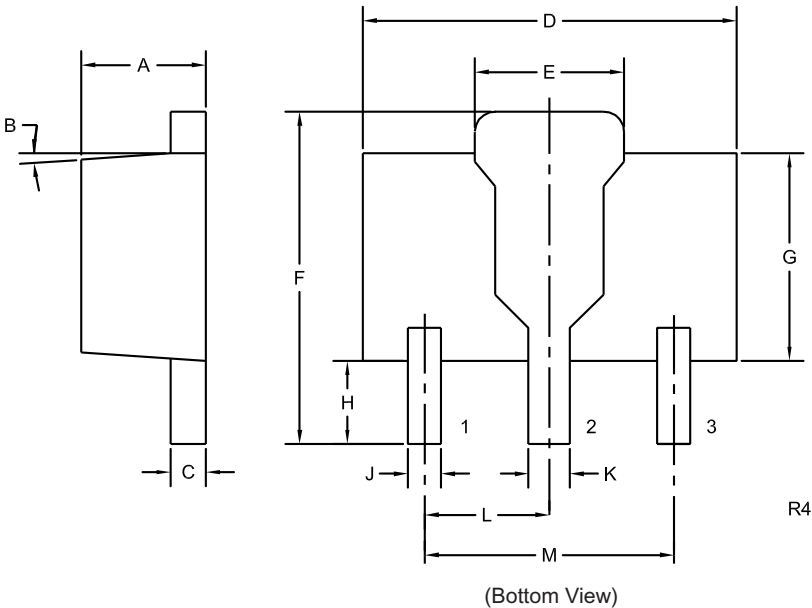
SURFACE MOUNT

PNP SILICON

DARLINGTON TRANSISTOR



SOT-89 CASE - MECHANICAL OUTLINE



LEAD CODE:
1) Emitter
2) Collector
3) Base

MARKING:
FULL PART NUMBER

DIMENSIONS				
SYMBOL	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.055	0.067	1.40	1.70
B	4°		4°	
C	0.014	0.018	0.35	0.46
D	0.173	0.185	4.40	4.70
E	0.064	0.074	1.62	1.87
F	0.146	0.177	3.70	4.50
G	0.090	0.106	2.29	2.70
H	0.028	0.051	0.70	1.30
J	0.014	0.019	0.36	0.48
K	0.017	0.023	0.44	0.58
L	0.059		1.50	
M	0.118		3.00	

SOT-89 (REV: R4)

R3 (23-February 2010)